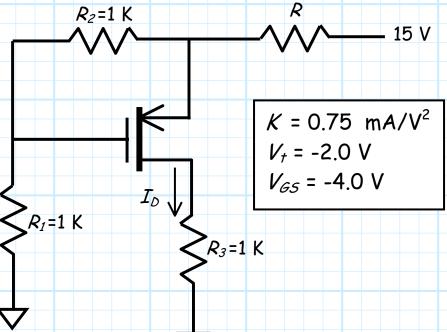
<u>Example: Another PMOS</u> <u>Circuit Analysis</u>

Consider the **PMOS** circuit below, where we know (somehow) that V_{GS} = -4.0 V, but don't know (for some reason) the value of resistor *R*.



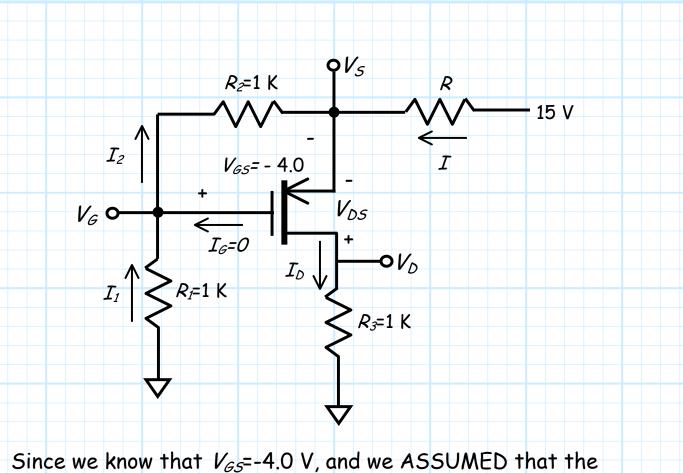
Let's see if we can determine the value of resistor R.

First, let's ASSUME that the MOSFET is in saturation, and therefore ENFORCE the drain current equation:

$$\mathcal{I}_{\mathcal{D}} = \mathcal{K} \left(\mathcal{V}_{\mathcal{GS}} - \mathcal{V}_{\mathcal{T}} \right)^2$$

Now we ANALYZE the circuit:





PMOS device was in saturation, we can directly determine the drain current I_D :

$$I_{D} = K (V_{GS} - V_{t})^{2}$$

= 0.75 (-4.0 - (-2.0))^{2}
= 0.75 (-4.0 + 2.0)^{2}
= 3 mA

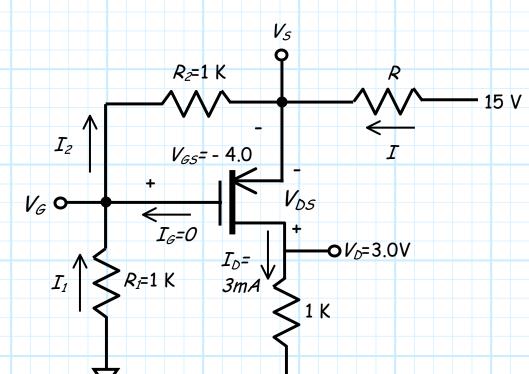
and thus the drain voltage V_D is:

$$V_{D} = 0.0 + I_{D}R_{3}$$

= 0.0 + (3.0)1.0
= 3.0 V

Q: OK, this first part was easy, but what do we do now? How can we determine the value of resistor R?

A: The key to "unlocking" this circuit analysis is recognizing that the potential difference across resistor R_2 is simply the voltage V_{GS} —and we **know** the value of V_{GS} (V_{GS} =-4.0V)!

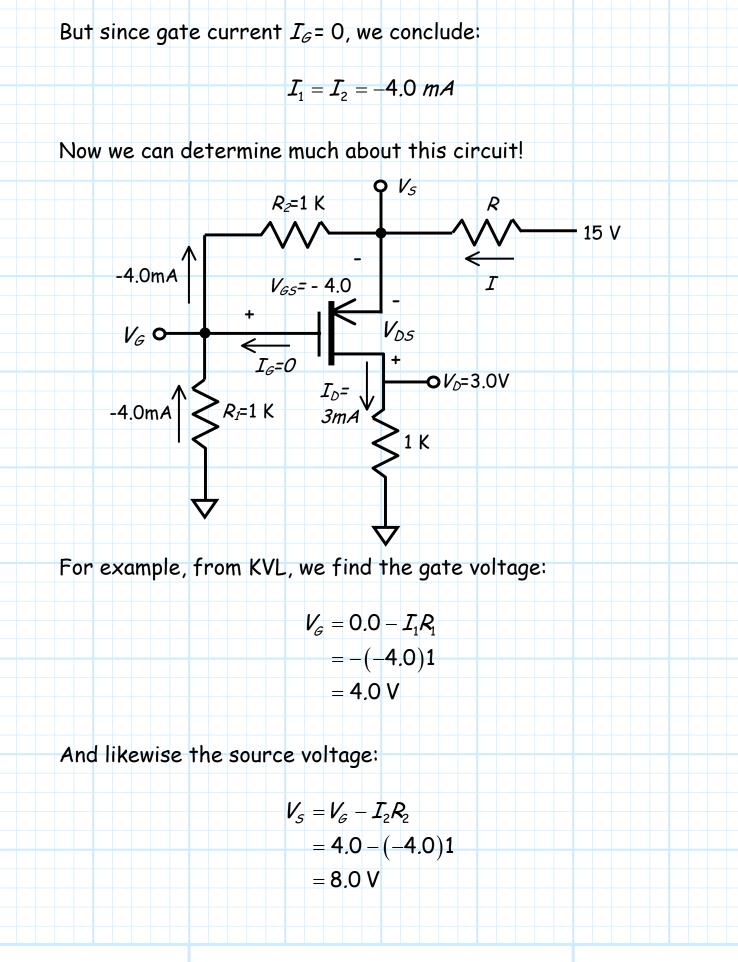


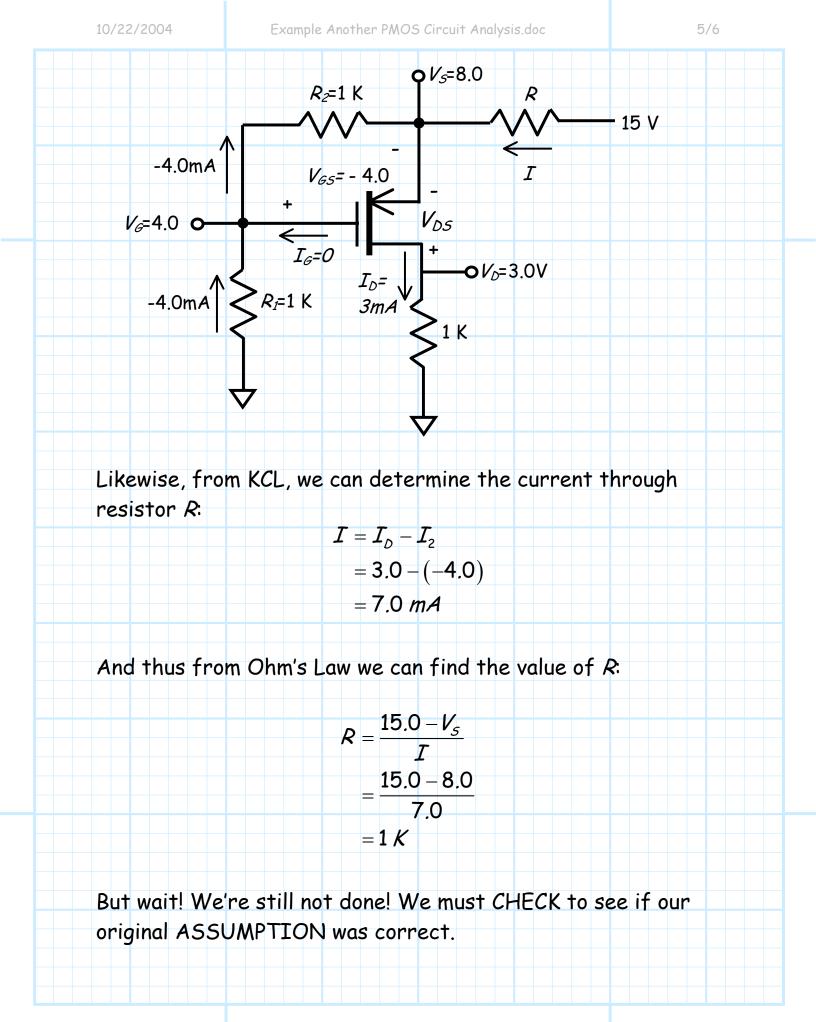
Thus, we can immediately determine that current I_2 is:

$$I_2 = \frac{V_{GS}}{R_2} = \frac{-4.0}{1} = -4.0 \ mA$$

Likewise, from KCL, we find:

 $I_1 + I_{\mathcal{G}} = I_{\mathcal{P}}$





First, we CHECK to see if the channel is induced:

 $V_{GS} = -4.0 < -2.0 = V_{t}$

Next, we CHECK to see if the channel is pinched off. Here, we note that $V_{DS} = V_D - V_S = 3.0 - 8.0 = -5.0$ V, and excess gate voltage is $V_{GS} - V_f = -4.0 - (-2.0) = -2.0$ V. Therefore:

$$V_{DS} = -5.0 < -2.0 = V_{GS} - V_{t}$$

Hence, our ASSUMPTION is correct, and R = 1K.